

**FEATURES OF OHMIC HEATING OF THE SILICONIZED
SILICON CARBIDE AT MEASUREMENT OF THERMAL
PROPERTIES IN THE FIELD OF HIGH TEMPERATURES**

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The silicified silicium carbide $\text{SiC}+\text{Si}$ is high-temperature material. However, heaters from the silicified silicium carbide usually are used at a temperature below 1600 K.

Basic circuit of the equipment on which features of ohmic heating of the siliconized silicon carbide are realized and investigated at temperatures over 1600 K are presented. It is shown that use of the personal computer original program with two-parameter (current and temperature) a feedback for regulation of tension brought to an exemplar, and an express inventory allowed to realize the steady steady thermal conditions necessary for determination of resistance. Specific electrical resistance of the siliconized silicon carbide is measured in temperature range 1200–2200 K.